

Application No.: 10/601,597

Docket No.: 2336-181

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-18. (canceled)

19. (currently amended) A GaN light emitting diode, comprising:  
a first conductive GaN clad layer with an upper surface provided with a first contact formed thereon;  
an active layer formed on a lower surface of the first conductive GaN clad layer;  
a second conductive GaN clad layer formed on a lower surface of the active layer;  
a conductive adhesive layer formed on the second conductive GaN clad layer; and  
a conductive substrate, with a lower surface provided with a second contact formed thereon,  
formed on a lower surface of the conductive adhesive layer;

~~The diode of claim 5,~~ wherein the conductive adhesive layer is made of Sn.

20. (currently amended) A GaN light emitting diode, comprising:  
a first conductive GaN clad layer with an upper surface provided with a first contact formed thereon;  
an active layer formed on a lower surface of the first conductive GaN clad layer;  
a second conductive GaN clad layer formed on a lower surface of the active layer;  
a conductive adhesive layer formed on the second conductive GaN clad layer; and  
a conductive substrate, with a lower surface provided with a second contact formed thereon,  
formed on a lower surface of the conductive adhesive layer;

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~~The diode of claim 5,~~ wherein the conductive adhesive layer is made of In.

21. **(currently amended)** A GaN light emitting diode, comprising:  
a first conductive GaN clad layer with an upper surface provided with a first contact formed thereon;  
an active layer formed on a lower surface of the first conductive GaN clad layer;  
a second conductive GaN clad layer formed on a lower surface of the active layer;  
a conductive adhesive layer formed on the second conductive GaN clad layer; and  
a conductive substrate, with a lower surface provided with a second contact formed thereon,  
formed on a lower surface of the conductive adhesive layer;

~~The diode of claim 5,~~ wherein the conductive adhesive layer is made of an Au-Ag alloy.

22-23. (canceled)